



PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN2905A	1
P _D	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

PNP General Purpose Amplifier (continued)

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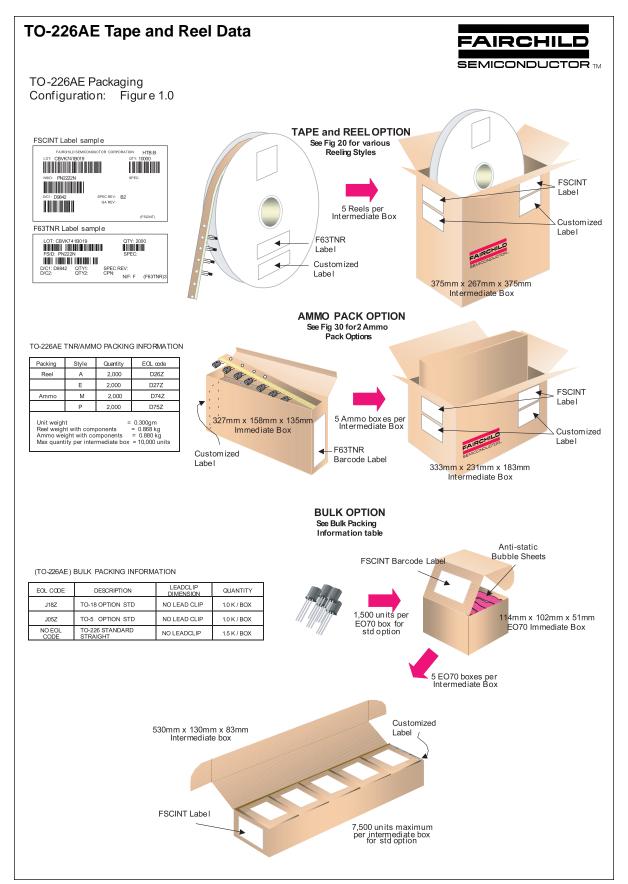
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Symbol	Parameter	Test Conditions	Min	Max	Units
	DA OTEDIOTIO				
	RACTERISTICS	I		1	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
I _B	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{BE} = 0.5 \text{ V}$		50	nA
I _{CEX}	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{BE} = 0.5 \text{ V}$		50	nA
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_{E} = 0$ $V_{CB} = 50 \text{ V}, I_{E} = 0, T_{A} = 150^{\circ}\text{C}$		0.01 10	μA μA
	ACTERISTICS DC Current Gain	L 04 mA V 40 V	75	T	
h _{FE}	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	100		
		$I_{\rm C} = 10 \text{mA}, V_{\rm CE} = 10 \text{V}$	100		
		$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}^*$	100	300	
\ /	Collector-Emitter Saturation Voltage*	$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}^*$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	50	0.4	V
V _{CE(sat)}	Collector-Efficier Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA*}$		1.3	V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		2.6	V
SMALL SI	GNAL CHARACTERISTICS				
f _T	Current Gain - Bandwidth Product	$I_C = 50 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	200		MHz
•					
C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 100 kHz		8.0	pF
C _{obo}	Output Capacitance Input Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0,$		30	pF pF
C _{obo}		$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 100 kHz $V_{EB} = 2.0 \text{ V}, I_{C} = 0,$			
C _{obo} C _{ibo}	Input Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 100 kHz $V_{EB} = 2.0 \text{ V}, I_{C} = 0,$			
C _{obo} C _{ibo} SWITCHII	Input Capacitance NG CHARACTERISTICS	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 100 kHz $V_{EB} = 2.0 \text{ V}, I_{C} = 0,$ f = 100 kHz		30	pF
C _{obo} C _{ibo} SWITCHII t _{on} t _d	Input Capacitance NG CHARACTERISTICS Turn-on Time	$\begin{split} &V_{CB} = 10 \text{ V, } I_{E} = 0, \\ &f = 100 \text{ kHz} \\ &V_{EB} = 2.0 \text{ V, } I_{C} = 0, \\ &f = 100 \text{ kHz} \end{split}$ $V_{CC} = 30 \text{ V, } I_{C} = 150 \text{ mA,}$		30	pF
C _{obo}	Input Capacitance NG CHARACTERISTICS Turn-on Time Delay Time	$\begin{split} &V_{CB} = 10 \text{ V, } I_{E} = 0, \\ &f = 100 \text{ kHz} \\ &V_{EB} = 2.0 \text{ V, } I_{C} = 0, \\ &f = 100 \text{ kHz} \end{split}$ $V_{CC} = 30 \text{ V, } I_{C} = 150 \text{ mA,}$		30 45 10	pF ns ns

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Fall Time

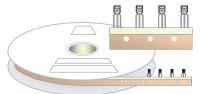
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.



TO-226AE Tape and Reel Data, continued

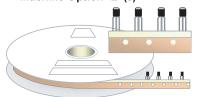
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

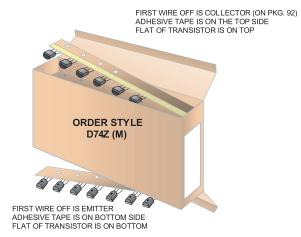
Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM



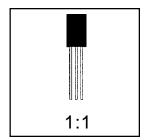
TO-226AE Tape and Reel Data, continued TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0 ITEM DESCRIPTION SYMBOL DIMENSION Base of Package to Lead Bend 0.098 (max) Component Height Hb 1.078 (+/- 0.050) User Direction of Feed 0.630 (+/- 0.020) Lead Clinch Height HO Component Base Height H1 0.748 (+/- 0.020) Component Alignment (side/side) Pd 0.040 (max) 0.031 (max) Component Alignment (front/back) Hd 0.500 (+/- 0.020) Component Pitch РО Feed Hole Pitch 0.500 (+/- 0.008) Hole Center to First Lead P1 0.150 (+0.009, -0.010) Hole Center to Component Center P2 0.247 (+/- 0.007) Lead Spread F1/F2 0.104 (+/- 0 010) Lead Thickness d 0.018 (+0.002, -0.003) 0.429 (max) Cut Lead Length Taped Lead Length 0.209 (+0.051, -0.052) L1 Taped Lead Thickness 0.032 (+/- 0.006) Carrier Tape Thickness t1 0.021 (+/- 0.006) TO-226AE Reel Carrier Tape Width 0.708 (+0.020, -0.019) W Configuration: Figure 5.0 Hold - down Tape Width wo 0.236 (+/- 0.012) 0.035 (max) Hold - down Tape position W1 0.360 (+/- 0.025) W2 Feed Hole Position 0.157 (+0.008, -0.007) Sprocket Hole Diameter DO 0.004 (max) Lead Spring Out S Note: All dmensions are in inches. D4 ITEM DESCRIPTION SYMBOL MINIMUM MAXIMUM Red Diameter 13975 14025 Arbor Hole Diameter (Standard) 1.200 D2 1.160 D2 0.650 0.700 (Small Hole) Core Diameter D3 3.100 3.300 Hub Recess Inner Diameter D4 3.100 Hub Recess Depth W 1 0.370 0.570 Range to Range Inner Width W2 1.630 1.690 Hub to Hub Center Width 2.090 WЗ Note: All dimensions are inches

TO-226AE Package Dimensions



TO-226AE (FS PKG Code 95, 99)





Scale 1:1 on letter size paper

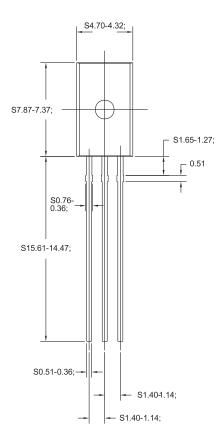
Dimensions shown below are in: inches [millimeters]

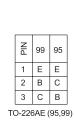
Part Weight per unit (gram): 0.300

- S1.52-1.02;

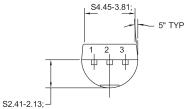
S7.73-7.10;

2" TYP





- S0.48-0.30;



For leadformed option ordering, refer to Tape & Reel data information.

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